Tuesday, September 27

9:15-12:00 Plenary (Main Convention Hall)

Lunch

1F 101	2F Convention Hall 200	2F 201A	2F 201B	2F 202A	2F 202B	3F 304	4F 401	4F 402	4F 403	4F 404	4F 405	4F 406
13:30-15:10 A-1:Novel 3D Structures and 2D Materials	**13:30-15:20** B-1:ReRAM-1	**13:30-15:15** C-1:Silicon Photonics I	**13:30-15:15 Area9&13** D-1:Physics and Technologies in 2D Materials	**13:30-15:00** E-1:SiC Devices & Characterization	**13:30-15:15** F-1:Organic Transistors	**13:30-15:15** G-1:Spin Dynamics	**13:30-15:15** H-1:Biosensors & Materials	**13:30-15:20** J-1:Advanced CMOS Image Sensors and Systems	**13:30-14:55** K-1:3D-TSV		**13:30-15:15** N-1:Narrow-gap III-V Materials and Devices	**13:30-15:20** O-1:Gate Stack and Interface Technology
Coffee Break												
15:40-17:30 Area1&3 A-2:Ferroelectric-gate TFETs and Vertical TFETs	**15:25-17:35 Area4&5&12** B-2:MRAM and its Applications	**15:40-17:25** C-2:Optical Sensor and its Application	**15:40-17:25** D-2:Nanostructure Synthesis and Devices		**15:40-17:25 Area10&15** F-2:Organic Photovoltaic Cells		**15:40-17:25** H-2:Nano Devices for Molecular & Biological Sensing	**15:40-17:40** J-2:2D Materials and Devices	**15:40-17:05** K-2:Cu Interconnect & CMP	**15:40-17:25** M-2:Qaumtum and Spin Technologies	**15:40-17:40 Area6&14** N-2:GaN & SiC Devices	

18:30-20:30 Banquet (Hotel Grand Shinonome)

Wednesday, September 28

1F 101	2F Convention Hall 200	2F 201A	2F 201B	2F 202A	2F 202B	3F 304	4F 401	4F 402	4F 403	4F 404	4F 405	4F 406
9:30-10:40 A-3:Transport Analysis and Modeling	**9:10-10:50** B-3:ReRAM-2/PRAM	**9:30-10:45** C-3:Silicon Photonics II		**9:30-10:45** E-3:SiC MOS Interface	**9:30-10:45** F-3:Organic Photonics	**9:30-10:45** G-3:Spintronics Devices	**9:30-10:45** H-3:Biomedical Micro Devices & Systems	**9:30-10:45** J-3:Low-dimensional Materials and Devices	**9:30-11:00 Area2&5** K-3:MEMS & Systems	**9:30-10:45** M-3:Novel Functional Devices	**9:30-10:45** N-3:Novel III-V Devices	**9:30-10:40** O-3:FinFET and Nanowire FET
Coffee Break												
11:00-12:00 Short Presentation Area3	**11:00-12:00 Short Presentation** Area4	**11:00-12:00 Short Presentation** Area7	**11:00-12:00 Short Presentation** Area8	**11:00-12:00 Short Presentation** Area14	**11:00-12:00 Short Presentation** Area15 **Short Presentation** Area10	**11:00-12:00 Short Presentation** Area12	**11:00-12:00 Short Presentation** Area11	**11:00-12:00 Short Presentation** Area13	**11:00-12:00 Short Presentation** Area2 **Short Presentation** Area5	**11:00-12:00 Short Presentation** Area9	**11:00-12:00 Short Presentation** Area6	**11:00-12:00 Short Presentation** Area1
Lunch												
13:30-14:40 A-4:Monolithic 3D and Reliability	**13:30-14:30** B-4:FeRAM/DRAM/MEMS	**13:30-14:45** C-4:Quantum Dot Devices	**13:30-14:45** D-4:Growth of Compound Semiconductors	**13:30-14:45** E-4:Group 4 Novel Devices	**13:30-14:45** F-4:Organic Thermoelectrics, Piezoelectrics and Ferroelectrics	**13:30-14:45** G-4:Spin Injection	**13:30-14:45 Area5&11** H-4:Advanced Imaging and Measurement Circuits for Medical and Bio Applications	**13:30-14:45** J-4:Silicon Photovoltaics I	**13:30-15:00 Area2&13** K-4:Organic & 2-D Materials	**13:30-14:45** M-4:Quantum Coherence	**13:30-14:45** N-4:GaN Device Technologies	**13:30-14:50** O-4:Ferroelectrics and Characterization
Coffee Break												

15:00-17:00 Poster Session
(102, Multi-Purpose Hall)

17:15-18:45 Rump Sessions
(201, 202)

Thursday, September 29

1F 101	2F Convention Hall 200	2F 201A	2F 201B	2F 202A	2F 202B	3F 304	4F 401	4F 402	4F 403	4F 404	4F 405	4F 406
9:30-11:00 A-5:Fully Depleted Structures	**9:30-10:50** B-5:Memory Hierarchy	**9:30-11:00 Area7&12** C-5:Electro/Spintronics Optical Devices	**9:30-10:45** D-5:Growth of Germanium-based Semiconductors		**9:30-10:45** F-5:Solution Processed Devices	**9:30-10:45** G-5:II-VI and III-V Compound Photovoltaics	**9:30-11:00** H-5:Nanosensing & Microfluidic Systems	**9:30-10:50** J-5:Advanced Functional Devices and System Architectures	**9:30-10:45** K-5:III-V Nanowires	**9:30-11:00** M-5:Bonding Technologies	**09:30-10:45 Area6&14** N-5:Novel Wide-Gap Materials & Devices	**9:30-10:45** O-5:Ultrathin Channel Engineering
Coffee Break												
11:15-12:25 A-6:TFETs	**11:15-12:15** B-6:Flash Memory	**11:15-12:45** C-6:Novel Spintronics Phenomena	**11:15-12:30** D-6:Nanostructures Synthesis and Properties	**11:15-12:30** E-6:Semiconductor Light Sources	**11:15-12:30** F-6:Organic Light Emitting Devices	**11:15-12:30** G-6:Silicon Photovoltaics II		**11:15-12:25** J-6:Advanced Low-Power Circuit Technologies for IoT Era	**11:15-12:30** K-6:Functional Nanowires		**11:15-12:45 Area6&14** N-6:Wide Band-Gap Devices	**11:15-12:40** O-6:Junction and Contact Technologies
Lunch												
14:00-15:40 A-7:TFET Variability	**13:40-15:50 Area4&9** B-7:Neuromorphic Computing											

Area Scope

- Area 1: Advanced LSI Processing & Materials Science
- Area 2: Interconnect Technologies and 3D Integration/ Sensor/ MEMS Integration/ Materials and Characterization
- Area 3: CMOS Devices / Device Physics
- Area 4: Advanced Memory Technology
- Area 5: Advanced Circuits and Systems
- Area 6: Compound Semiconductor Electron Devices & Related Technologies
- Area 7: Photonic Devices and Related Technologies
- Area 8: Advanced Material Synthesis and Crystal Growth Technology
- Area 9: Physics and Applications of Novel Functional Devices and Materials
- Area 10: Organic Materials Science, Device Physics, Applications and Printed Technologies
- Area 11: Sensors and Materials for Biology, Chemistry and Medicine
- Area 12: Spintronics Materials and Devices
- Area 13: Applications of Nanotubes, Nanowires, and Graphene and related 2D materials
- Area 14: Power Devices and Materials
- Area 15: Photovoltaic Materials and Devices